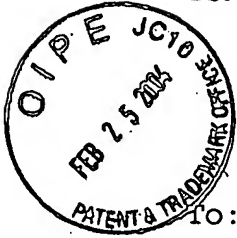


TSMC-03-395



February 18, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/728,215 12/04/03 |

Yi-Lung Cheng et al.

NOVEL METHOD TO DEPOSIT CARBON
DOPED SiO₂ FILMS WITH IMPROVED
FILM QUALITY

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on February 23, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 2/23/04

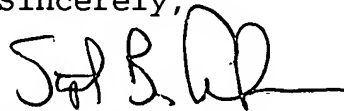
U.S. Patent Application Publication US 2003/0032292 A1 to Noguchi, "Fabrication Method of Semiconductor Integrated Circuit Device," discusses a Black Diamond film formed by a process involving trimethylsilane and oxygen.

U.S. Patent 6,372,632 to Yu et al., "Method to Eliminate Dishing of Copper Interconnects by the Use of a Sacrificial Oxide Layer," describes an organosilane such as trimethylsilane and a compensatory gas including Ar, O₂, CH₄, N₂O, N₂, H₂, etc, employed to deposit a low k dielectric layer.

U.S. Patent 6,312,793 to Grill et al., "Multiphase Low Dielectric Constant Material," describes a dual phase dielectric layer in which a first phase is comprised of SiCOH.

U.S. Patent 6,541,397 to Bencher, "Removable Amorphous Carbon CMP Stop," discusses a siliconoxycarbide layer deposited with one or more organosilicon compounds, an oxidizing gas, and an inert gas at 50-5000 sccm.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman".

Stephen B. Ackerman,
Reg. No. 37761

(Use several sheets if necessary)

Application Number

10 | 728,215

Yi-Lung Cheng et al.

12/04/03

Group Meeting

A circular stamp from the Office of Intellectual Property (OIP). The text "OIP" is at the top, "FEB 25 2004" is in the center, and "PATENT & TRADEMARK OFFICE" is at the bottom. The stamp is partially cut off by the right edge of the page.

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FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

-	US Patent App. Pub. US 2003/0032292 A1 to Nozuchi.
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DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant